

# EMB3 / UMB3N / IMB3A

PNP -100mA -50V Complex Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

Parameter	Tr1 and Tr2
V <sub>CEO</sub>	-50V
I <sub>C(MAX.)</sub>	-100mA
R <sub>1</sub>	<b>4.7k</b> Ω

### Features

- 1) Built-In Biasing Resistors.
- 2) Two DTA143T chips in one package.
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

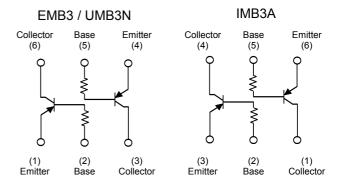
# Application

Inverter circuit, Interface circuit, Driver circuit

# Outline

EMT6 (1) (2) (3) (4)	UMT6
EMB3 (SC-107C)	UMB3N SOT-363 (SC-88)
SMT6 (3)(2)(1)(4)(5)(6)	
IMB3A SOT-457 (SC-74)	

#### Inner circuit



#### Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMB3	EMT6	1616	T2R	180	8	8,000	B3
UMB3N	UMT6	2021	TR	180	8	3,000	B3
IMB3A	SMT6	2928	T108	180	8	3,000	B3

## •Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Paramet	er	Symbol	Values	Unit
Collector-base voltage		V <sub>CBO</sub>	-50	V
Collector-emitter voltage		V <sub>CEO</sub>	-50	V
Emitter-base voltage		V <sub>EBO</sub>	-5	V
Collector current		۲ ا <sub>C(MAX.)</sub> *1	-100	mA
Collector Power dissipation	EMB3 / UMB3N	- P <sub>D</sub> <sup>*2</sup>	150 (Total) <sup>*3</sup>	mW
ІМВЗА			300 (Total) <sup>*4</sup>	mW
Junction temperature		Тj	150	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +150	°C

# •Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	$BV_{CBO}$	$I_C = -50 \mu A$	-50	-	-	V
Collector-emitter breakdown voltage	$BV_{CEO}$	I <sub>C</sub> = –1mA	-50	-	-	V
Emitter-base breakdown voltage	$BV_{EBO}$	I <sub>E</sub> = -50μA	-5	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -50V	-	-	-0.5	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V	-	-	-0.5	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> / I <sub>B</sub> = -5mA / -0.25mA	-	-	-0.3	V
DC current gain	h <sub>FE</sub>	$V_{CE}$ = -5V , $I_{C}$ = -1mA ,	100	250	600	-
Input resistance	R <sub>1</sub>	-	3.29	4.7	6.11	kΩ
Transition frequency	f <sub>T</sub> *1	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz	-	250	-	MHz

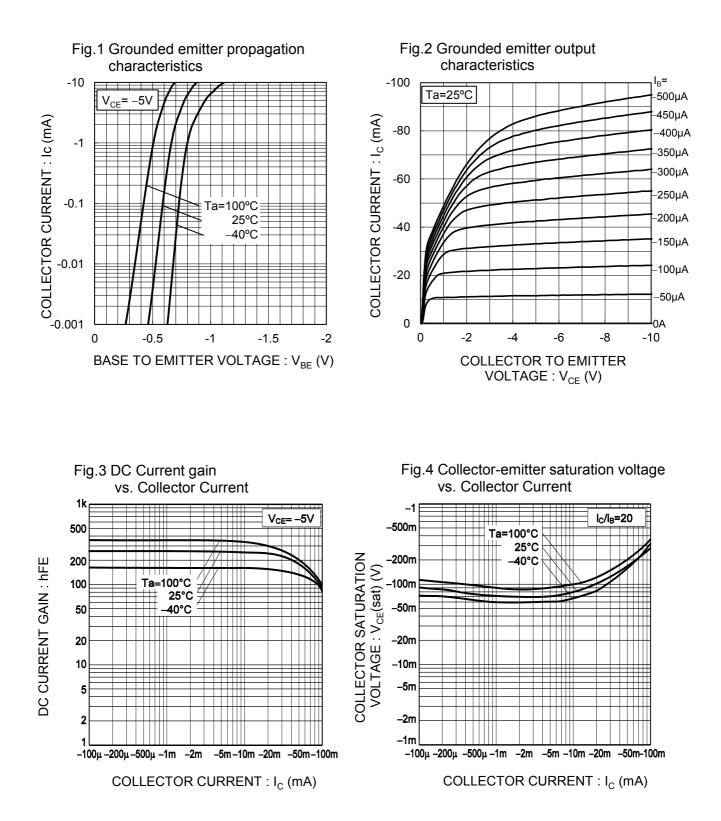
\*1 Characteristics of built-in transistor

\*2 Each terminal mounted on a reference footprint

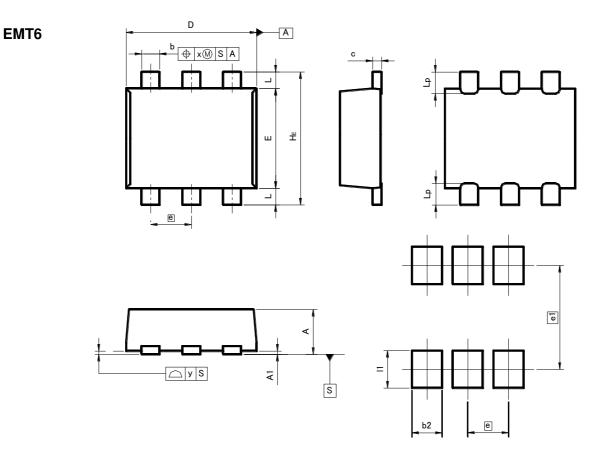
\*3 120mW per element must not be exceeded.

\*4 200mW per element must not be exceeded.

#### •Electrical characteristic curves(Ta = 25°C)



#### •Dimensions (Unit : mm)



#### Patterm of terminal position areas

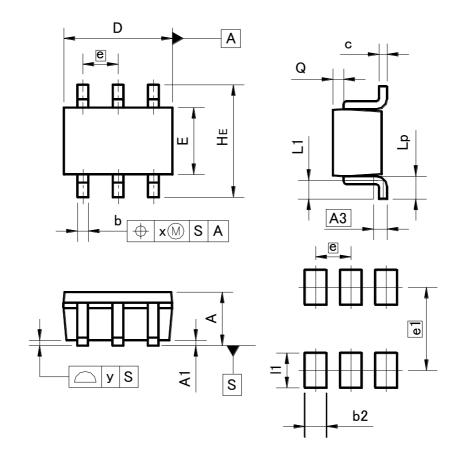
DIM	MILIM	ETERS	INC	HES	
	MIN	MAX	MIN	MAX	
A1	0.00	0.10	0	0.004	
A	0.45	0.55	0.018	0.022	
b	0.17	0.27	0.007	0.011	
с	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
E	1.10	1.30	0.043	0.051	
е	0.	50	0.02		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	_	0.35	-	0.014	
x	-	0.10	-	0.004	
У	-	0.10	-	0.004	

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	1.25		0.049		
b2	-	- 0.37		0.015	
1	1	0.45	-	0.018	

Dimension in mm/inches

#### •Dimensions (Unit : mm)

UMT6



#### Patterm of terminal position areas

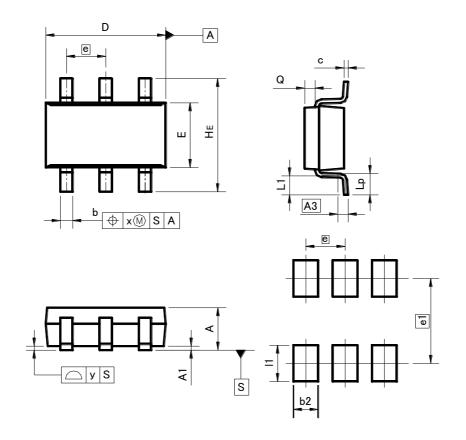
DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
А	0.80	1.00	-	0.039	
A1	0.00	0.10	0	0.004	
A3	0.5	25	0.0	01	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
Е	1.15	1.35	0.045	0.053	
е	0.0	65	0.03		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.02	
Lp	0.25	0.55	0.01	0.022	
Q	0.10	0.30	0.004	0.012	
х	_	0.10	_	0.004	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
e1	1.55		0.06	
b2	-	0.40	-	0.016
1	-	0.65	-	0.026

Dimension in mm/inches

#### •Dimensions (Unit : mm)

SMT6



#### Patterm of terminal position areas

DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0	0.004	
A3	0.2	25	0.0	01	
b	0.25	0.40	0.01	0.016	
С	0.09	0.25	0.004	0.01	
D	2.80	3.00	0.11	0.118	
Е	1.50	1.80	0.059	0.071	
е	0.9	95	0.04		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.20	_	0.008	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INC	HES	
DIM	MIN	MIN MAX		MAX	
e1	2.10		0.08		
b2		0.60	-	0.024	
1	_	0.90	_	0.035	

Dimension in mm/inches

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